

RT3CLLM

Compound Transistor
For Low Frequency Amplify Application
Silicon Npn Epitaxial Type

DESCRIPTION

RT3CLLM is a compound transistor built with two 2SC3052 chips in SC-88 package.

FEATURE

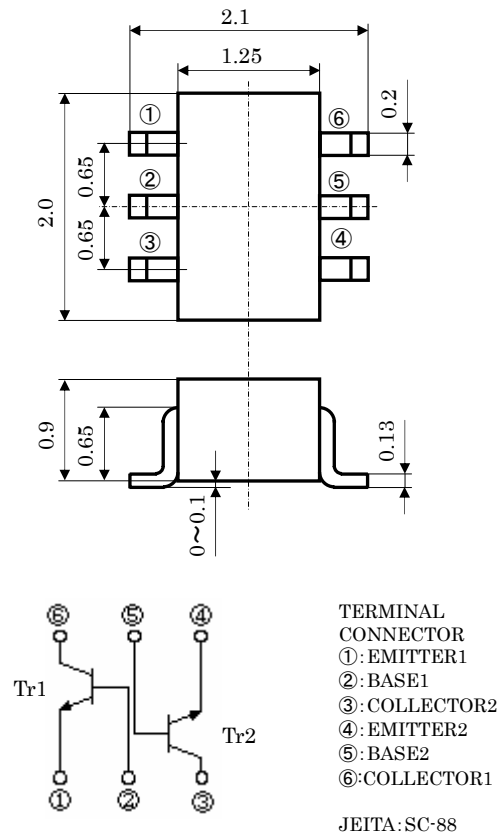
- Silicon npn epitaxial type
- Each transistor elements are independent.
- Mini package for easy mounting

APPLICATION

For low frequency amplify application

OUTLINE DRAWING

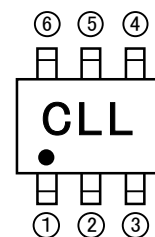
Unit: mm



MAXIMUM RATING (Ta=25°C)

| SYMBOL | PARAMETER | RATING | UNIT |
|-----------------------|---------------------------------|----------|------|
| V _{CB0} | Collector to Base voltage | 50 | V |
| V _{EB0} | Emitter to Base voltage | 6 | V |
| V _{CEO} | Collector to Emitter voltage | 50 | V |
| I _C | Collector current | 200 | mA |
| P _{C(Total)} | Collector dissipation (Ta=25°C) | 150 | mW |
| T _j | Junction temperature | +125 | °C |
| T _{stg} | Storage temperature | -55~+125 | °C |

MARKING



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ELECTRICAL CHARACTERISTICS (Ta=25°C)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|----------|---|-----------------------------------|--------|-----|-----|------|
| | | | Min | Typ | Max | |
| V(BR)CEO | Collector to Emitter break down voltage | IC=100 μ A, RBE=∞ | 50 | - | - | V |
| ICBO | Collector cut off current | VCB=50V, IE=0 | - | - | 0.1 | μ A |
| IEBO | Emitter cut off current | VEB=6V, IC=0 | - | - | 0.1 | μ A |
| hFE* | DC forward current gain | VCE=6V, IC=1mA | 150 | - | 800 | - |
| hFE | DC forward current gain | VCE=6V, IC=0.1mA | 90 | - | - | - |
| VCE(sat) | Collector to Emitter saturation voltage | IC=100mA, IB=10mA | - | - | 0.3 | V |
| fT | Gain band width product | VCE=6V, IE=-10mA | - | 200 | - | MHZ |
| Cob | Collector output capacitance | VCB=6V, IE=0, f=1MHz | - | 2.5 | - | pF |
| NF | Noise figure | VCE=6V, IE=-0.1mA, f=1kHz, RG=2kΩ | - | - | 15 | dB |

* : It shows hFE classification in right table.

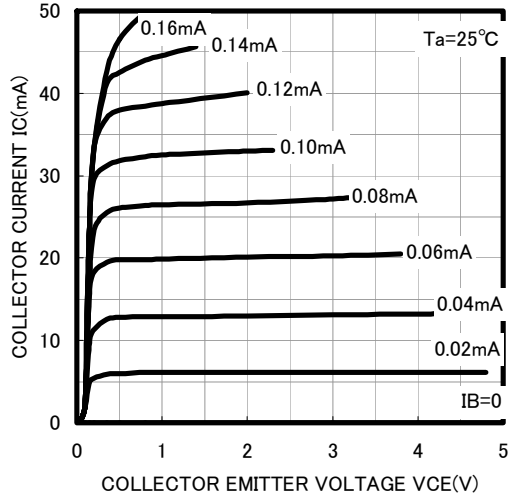
| Item | E | F | G |
|------|---------|---------|---------|
| hFE | 150~300 | 250~500 | 400~800 |

RT3CLLM

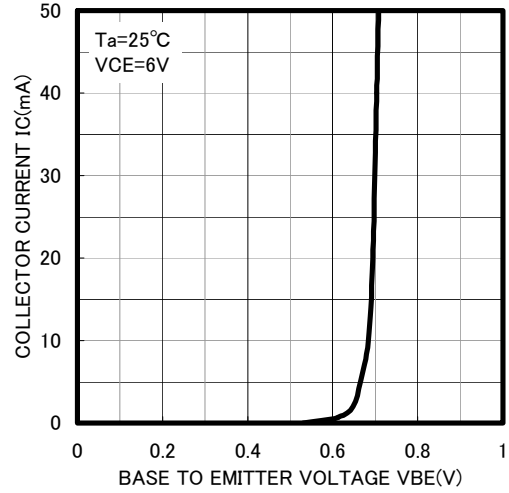
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TYPICAL CHARACTERISTICS

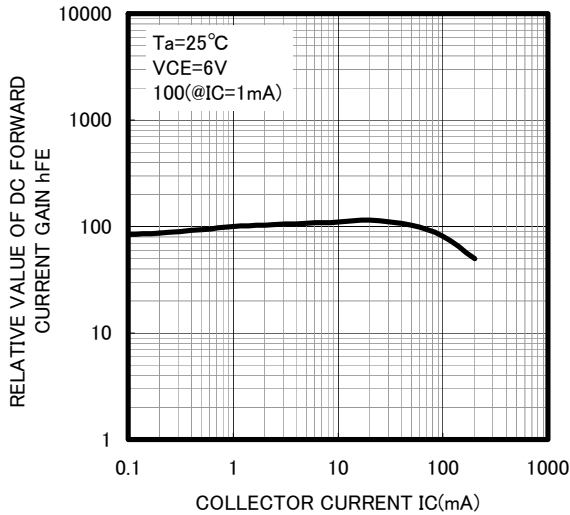
COMMON EMITTER OUTPUT



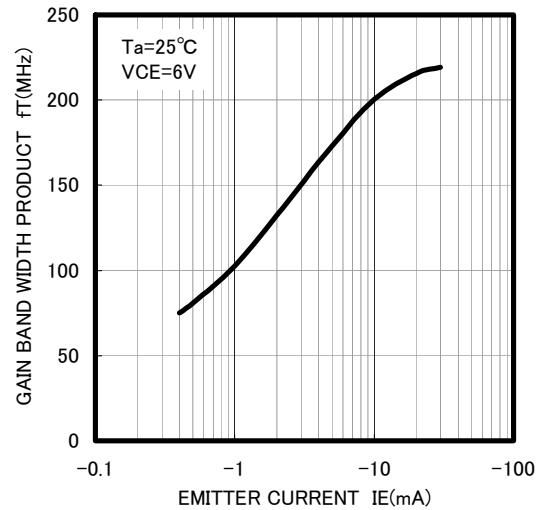
COMMON EMITTER TRANSFER



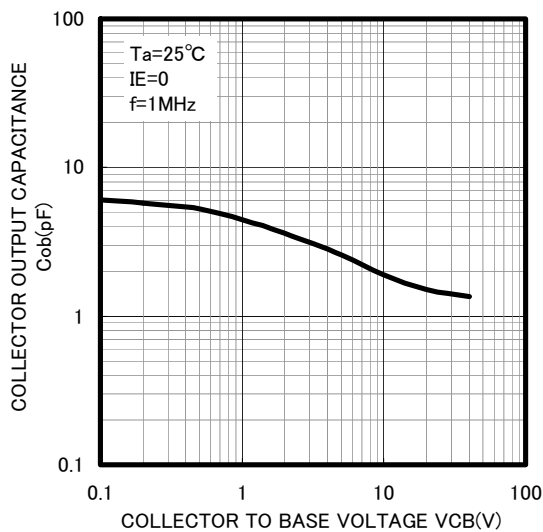
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



GAIN BAND WIDTH PRODUCT VS. EMITTER CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE





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